L Number	Hits	Search Text	DB	Time stamp
-	226	semiconduct$3 and HMDS with prim$3	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/19 18:13
-	2005	semiconduct$3 same (defect$3 and (resist or photoresist or photopolymer$7) and develop$4)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/20 08:26
-	10	(semiconduct$3 same (defect$3 and (resist or photoresist or photopolymer$7) and develop$4)) and (HMDS or hexamethyldisilazane or hexamethyl adj disilazane or silazane) same prim$3	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/21 19:47
-	6246	(semiconduct$3 or silicon or "Si" or wafer) same ((defect$3 or residue) and (resist or photoresist or photopolymer$7) and develop$4)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/20 09:05
-	1152	((semiconduct$3 or silicon or "Si" or wafer) same ((defect$3 or residue) and (resist or photoresist or photopolymer$7) and develop$4)) and (resist or photoresist or photopolymer$7) same (develop$4 or rins$3) same (spin$4 or rotat$3 or turn$3 or speed$3)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/20 09:21
-	12	((semiconduct$3 or silicon or "Si" or wafer) same ((defect$3 or residue) and (resist or photoresist or photopolymer$7) and develop$4)) and (resist or photoresist or photopolymer$7) same (develop$4 or rins$3) same (spin$4 or rotat$3 or turn$3 or speed$3) and ((develop$4 or rins$3) or (spin$4 or rotat$3 or turn$3 or speed$3)) same (exhaust$3 or air) near5 (velocit$3 or speed$3)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/20 09:11
-	130	((semiconduct$3 or silicon or "Si" or wafer) same ((defect$3 or residue) and (resist or photoresist or photopolymer$7) and develop$4)) and (resist or photoresist or photopolymer$7) same (develop$4 or rins$3) same (spin$4 or rotat$3 or turn$3) near5 (velocit$3 or speed$3)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/20 09:22
-	11	(((semiconduct$3 or silicon or "Si" or wafer) same ((defect$3 or residue) and (resist or photoresist or photopolymer$7) and develop$4)) and (resist or photoresist or photopolymer$7) same (develop$4 or rins$3) same (spin$4 or rotat$3 or turn$3) near5 (velocit$3 or speed$3)) and (develop$4 or rins$3 or spin$4 or rotat$3 or turn$3) same (exhaust$3 or air or gas or sweep$ or flow$3 or pass$3) near5 (velocit$3 or speed$3)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/20 09:24
-	1347	((semiconduct$3 or silicon or "Si" or wafer) same ((defect$3 or residue) and (resist or photoresist or photopolymer$7) and develop$4)) and (resist or photoresist or photopolymer$7) same (develop$4 or rins$3 or clean$3 or dry$3) same (spin$4 or rotat$3 or turn$3 or speed$3)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/20 09:21

-		179	((semiconduct$3 or silicon or "Si" or wafer) same ((defect$3 or residue) and (resist or photoresist or photopolymer$7) and develop$4)) and (resist or photoresist or photopolymer$7) same (develop$4 or rins$3 or clean$3 or dry$3) same (spin$4 or rotat$3 or turn$3) near5 (velocit$3 or speed$3)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/20 09:22
-		11	(((semiconduct$3 or silicon or "Si" or wafer) same ((defect$3 or residue) and (resist or photoresist or photopolymer$7) and develop$4)) and (resist or photoresist or photopolymer$7) same (develop$4 or rins$3) same (spin$4 or rotat$3 or turn$3) near5 (velocit$3 or speed$3)) and (develop$4 or rins$3 or clean$3 or dry$3 or spin$4 or rotat$3 or turn$3) same (exhaust$3 or air or gas or sweep$ or flow$3 or pass$3) near5 (velocit$3 or speed$3)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/20 17:06
-		1091	((resist or photoresist or photopolymer$7) same (develop$4 or rins$3 or clean$3 or remov$3 or residue or rubbish or debris) same (spin$4 or spun or rotat$3 or turn$3) near5 (velocit$3 or speed$3)) not ((((semiconduct$3 or silicon or "Si" or wafer) same ((defect$3 or residue) and (resist or photoresist or photopolymer$7 and develop$4)) and (resist or photoresist or photopolymer$7) same (develop$4 or rins$3) same (spin$4 or rotat$3 or turn$3) near5 (velocit$3 or speed$3)) and (develop$4 or rins$3 or clean$3 or dry$3 or spin$4 or rotat$3 or turn$3) same (exhaust$3 or air or gas or sweep$ or flow$3 or pass$3) near5 (velocit$3 or speed$3))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/20 17:12
-		825	(((resist or photoresist or photopolymer$7) same (develop$4 or rins$3 or clean$3 or remov$3 or residue or rubbish or debris) same (spin$4 or spun or rotat$3 or turn$3) near5 (velocit$3 or speed$3)) not ((((semiconduct$3 or silicon or "Si" or wafer) same ((defect$3 or residue) and (resist or photoresist or photopolymer$7) and develop$4)) and (resist or photoresist or photopolymer$7) same (develop$4 or rins$3 same (spin$4 or rotat$3 or turn$3) near5 (velocit$3 or speed$3)) and (develop$4 or rins$3 or clean$3 or dry$3 or spin$4 or rotat$3 or turn$3) same (exhaust$3 or air or gas or sweep$ or flow$3 or pass$3) near5 (velocit$3 or speed$3)) and (semiconduct$3 or wafer or silicon or "Si")	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/20 17:15

–	320	(((((resist or photoresist or photopolymer$7) same (develop$4 or rins$3 or clean$3 or remov$3 or residue or rubbish or debris) same (spin$4 or spun or rotat$3 or turn$3) near5 (velocit$3 or speed$3)) not (((((semiconduct$3 or silicon or "Si" or wafer) same ((defect$3 or residue) and (resist or photoresist or photopolymer$7) and develop$4)) and (resist or photoresist or photopolymer$7) same (develop$4 or rins$3) same (spin$4 or rotat$3 or turn$3) near5 (velocit$3 or speed$3)) and (develop$4 or rins$3 or clean$3 or dry$3 or spin$4 or rotat$3 or turn$3) same (exhaust$3 or air or gas or sweep$ or flow$3 or pass$3) near5 (velocit$3 or speed$3))) and (semiconduct$3 or wafer or silicon or "Si")) and (spin$4 or spun or rotat$3 or turn$3) same (exhaust$3 or air or sweep$3 or swept or inert or gas$4)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/20 17:18
–	39	(((((resist or photoresist or photopolymer$7) same (develop$4 or rins$3 or clean$3 or remov$3 or residue or rubbish or debris) same (spin$4 or spun or rotat$3 or turn$3) near5 (velocit$3 or speed$3)) not (((((semiconduct$3 or silicon or "Si" or wafer) same ((defect$3 or residue) and (resist or photoresist or photopolymer$7) and develop$4)) and (resist or photoresist or photopolymer$7) same (develop$4 or rins$3) same (spin$4 or rotat$3 or turn$3) near5 (velocit$3 or speed$3)) and (develop$4 or rins$3 or clean$3 or dry$3 or spin$4 or rotat$3 or turn$3) same (exhaust$3 or air or gas or sweep$ or flow$3 or pass$3) near5 (velocit$3 or speed$3))) and (semiconduct$3 or wafer or silicon or "Si")) and (spin$4 or spun or rotat$3 or turn$3) same (exhaust$3 or air or sweep$3 or swept or inert or gas$4)) and (resist or photoresist or photopolym$7 same (prim$3 or pre adj treat$3 or pretreat$3)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/23 16:44
–	1	("4556785").PN.	USPAT; US-PGPUB	2003/06/21 16:17
–	443	((resist or photoresist or photopolymer$7) and (semiconduct$3 or silicon or "Si" or wafer or substrate) same (HMDS or hexamethyldisilazane or hexamethyl adj disilazane) same (prim$3 or pretreat$4 or pre adj treat$4)) not ((semiconduct$3 same (defect$3 and (resist or photoresist or photopolymer$7) and develop$4)) and (HMDS or hexamethyldisilazane or hexamethyl adj disilazane or silazane) same prim$3)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/21 19:53
–	237	((resist or photoresist or photopolymer$7) and (semiconduct$3 or silicon or "Si" or wafer or substrate) same (HMDS or hexamethyldisilazane or hexamethyl adj disilazane) same (prim$3 or pretreat$4 or pre adj treat$4)) not ((semiconduct$3 same (defect$3 and (resist or photoresist or photopolymer$7) and develop$4)) and (HMDS or hexamethyldisilazane or hexamethyl adj disilazane or silazane) same prim$3)) and ((HMDS or hexamethyldisilazane or hexamethyl adj disilazane or silazane) or prim$3) same (seconds or "sec")	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/21 20:06

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		85	(((resist or photoresist or photopolymer$7) and (semiconduct$3 or silicon or "Si" or wafer or substrate) same (HMDS or hexamethyldisilazane or hexamethyl adj disilazane) same (prim$3 or pretreat$4 or pre adj treat$4)) not ((semiconduct$3 same (defect$3 and (resist or photoresist or photopolymer$7) and develop$4)) and (HMDS or hexamethyldisilazane or hexamethyl adj disilazane or silazane) same prim$3)) and (((HMDS or hexamethyldisilazane or hexamethyl adj disilazane or silazane) or prim$3) near5 vapor) same (seconds or "sec")	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/21 20:08
		6097	((resist or photoresist or photopolymer$7) same ((develop$4) and (rins$3 or wash$3 or clean$3 or remov$3 or residue or rubbish or debris)) same (spin$4 or spun or rotat$3 or turn$3)) not ((((((resist or photoresist or photopolymer$7) same (develop$4 or rins$3 or clean$3 or remov$3 or residue or rubbish or debris) same (spin$4 or spun or rotat$3 or turn$3) near5 (velocit$3 or speed$3)) not ((((semiconduct$3 or silicon or "Si" or wafer) same ((defect$3 or residue) and (resist or photoresist or photopolymer$7) and develop$4)) and (resist or photoresist or photopolymer$7) same (develop$4 or rins$3) same (spin$4 or rotat$3 or turn$3) near5 (velocit$3 or speed$3)) and (develop$4 or rins$3 or clean$3 or dry$3 or spin$4 or rotat$3 or turn$3) same (exhaust$3 or air or gas or sweep$ or flow$3 or pass$3) near5 (velocit$3 or speed$3))) and (semiconduct$3 or wafer or silicon or "Si")) and (spin$4 or spun or rotat$3 or turn$3) same (exhaust$3 or air or sweep$3 or swept or inert or gas$4)) and (resist or photoresist or photopolym$7) same (prim$3 or pre adj treat$3 or pretreat$3))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/23 16:57

| | | 721 | 430/311,326-327,329.ccls. and (((resist or photoresist or photopolymer$7) same ((develop$4) and (rins$3 or wash$3 or clean$3 or remov$3 or residue or rubbish or debris)) same (spin$4 or spun or rotat$3 or turn$3)) not ((((resist or photoresist or photopolymer$7) same (develop$4 or rins$3 or clean$3 or remov$3 or residue or rubbish or debris) same (spin$4 or spun or rotat$3 or turn$3) near5 (velocit$3 or speed$3)) not (((semiconduct$3 or silicon or "Si" or wafer) same ((defect$3 or residue) and (resist or photoresist or photopolymer$7) and develop$4)) and (resist or photoresist or photopolymer$7) same (develop$4 or rins$3) same (spin$4 or rotat$3 or turn$3 near5 (velocit$3 or speed$3)) and (develop$4 or rins$3 or clean$3 or dry$3 or spin$4 or rotat$3 or turn$3 same (exhaust$3 or air or gas or sweep$ or flow$3 or pass$3 near5 (velocit$3 or speed$3)) and (semiconduct$3 or wafer or silicon or "Si") and (spin$4 or spun or rotat$3 or turn$3 same (exhaust$3 or air or sweep$3 or swept or inert or gas$4)) and (resist or photoresist or photopolym$7) same (prim$3 or pre adj treat$3 or pretreat$3))) | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/06/23 16:56 |
| — | | 141 | (430/311,326-327,329.ccls. and (((resist or photoresist or photopolymer$7) same ((develop$4) and (rins$3 or wash$3 or clean$3 or remov$3 or residue or rubbish or debris) same (spin$4 or spun or rotat$3 or turn$3) not ((((resist or photoresist or photopolymer$7) same (develop$4 or rins$3 or clean$3 or remov$3 or residue or rubbish or debris) same (spin$4 or spun or rotat$3 or turn$3 near5 (velocit$3 or speed$3)) not (((semiconduct$3 or silicon or "Si" or wafer) same ((defect$3 or residue) and (resist or photoresist or photopolymer$7) and develop$4)) and (resist or photoresist or photopolymer$7) same (develop$4 or rins$3) same (spin$4 or rotat$3 or turn$3 near5 (velocit$3 or speed$3) and (develop$4 or rins$3 or clean$3 or dry$3 or spin$4 or rotat$3 or turn$3 same (exhaust$3 or air or gas or sweep$ or flow$3 or pass$3) near5 (velocit$3 or speed$3)) and (semiconduct$3 or wafer or silicon or "Si") and (spin$4 or spun or rotat$3 or turn$3 same (exhaust$3 or air or sweep$3 or swept or inert or gas$4)) and (resist or photoresist or photopolym$7 same (prim$3 or pre adj treat$3 or pretreat$3)) and (rins$3 or wash$3 or clean$3 or remov$3 or residue or rubbish or debris same (revolution or "rpm") | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/06/24 11:47 |